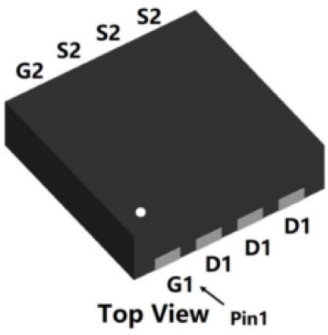
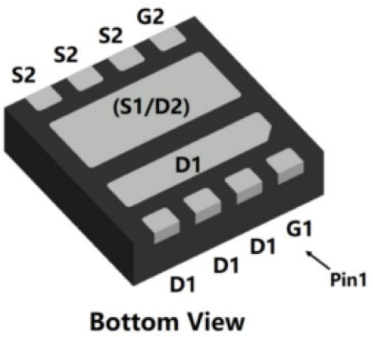
N-Channel and N-Channel Complementary MOSFET

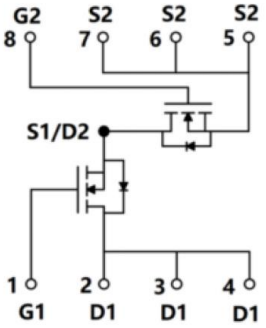


Top View



Bottom View

DFN3030-8L



Product Summary

NMOS(Die1)

- V_{DS} 30V
- I_D 30A
- $R_{DS(ON)}$(at V_{GS}=10V) ＜10mΩ
- $R_{DS(ON)}$(at V_{GS}=4.5V) ＜19.5mΩ

NMOS(Die2)

- V_{DS} 30V
- I_D 40A
- $R_{DS(ON)}$(at V_{GS}=10V) ＜6.5mΩ
- $R_{DS(ON)}$(at V_{GS}=4.5V) ＜15mΩ

General Description

- Dual Asymmetric N-Channel
- High Current Capability
- Low Gate Charge
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- DC/DC Converters in Computing, Servers
- Isolated DC/DC Converters in Telecom and Industrial

■ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter		Symbol	NMOS(Die1)	NMOS(Die2)	Unit
Drain-source Voltage		V_{DS}	30	30	V
Gate-source Voltage		V_{GS}	±20	±20	V
Drain Current	T_A=25℃	I_D	9	11	A
	T_A=100℃		5	7	
	T_C=25℃		30	40	
	T_C =100℃		19	25	
Pulsed Drain Current [A]		I_{DM}	120	160	A
Avalanche energy [B]		EAS	42.2	60	mJ
Total Power Dissipation [C]	T_A=25℃	P_D	1.56	1.66	W
	T_A=100℃		0.62	0.66	
	T_C=25℃		17.3	20.8	
	T_C =100℃		6.9	8.3	
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	-55～+150	℃

■Thermal resistance

Parameter		Symbol	NMOS(Die1)		NMOS(Die2)		Units
			Typ	Max	Typ	Max	
Thermal Resistance Junction-to-Ambient [D]	Steady-State	$R_{\theta JA}$	67	80	62	75	℃/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	6	7.2	5	6	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
QD3622A	F1	QD3622A	3000	30000	120000	13“ reel

■ NMOS(Die1) Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V	-	-	1	μA
		V_{DS}=30V, V_{GS}=0V, Tj=150℃	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1.1	1.5	2.2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=13A	-	7.5	10	mΩ
		V_{GS}=4.5V, I_D=10A	-	14	19.5	
Diode Forward Voltage	V_{SD}	I_S=10A, V_{GS}=0V	-	-	1.2	V
Gate resistance	R_G	f=1MHz	-	3	-	Ω
Maximum Body-Diode Continuous Current	I_S		-	-	30	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=15V, V_{GS}=0V, f=1MHz	-	1020	-	pF
Output Capacitance	C_{oss}		-	140	-	
Reverse Transfer Capacitance	C_{rss}		-	125	-	
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V, V_{DS}=15V, I_D=13A	-	20.7	-	nC
Gate-Source Charge	Q_{gs}		-	3.8	-	
Gate-Drain Charge	Q_{gd}		-	5.3	-	
Reverse Recovery Charge	Q_{rr}	I_F=13A, di/dt=100A/us	-	161	-	nC
Reverse Recovery Time	t_{rr}		-	136	-	ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V, V_{DD}=15V, I_D=13A R_{GEN}=2.2Ω	-	8.2	-	ns
Turn-on Rise Time	t_r		-	53.9	-	
Turn-off Delay Time	$t_{D(off)}$		-	18.4	-	
Turn-off fall Time	t_f		-	2.9	-	

■ NMOS(Die2) Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V	-	-	1	μA
		V_{DS}=30V, V_{GS}=0V, Tj=150℃	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1.1	1.5	2.2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=15A	-	5	6.5	mΩ
		V_{GS}=4.5V, I_D=10A	-	11	15	
Diode Forward Voltage	V_{SD}	I_S=10A, V_{GS}=0V	-	-	1.2	V
Gate resistance	R_G	f=1MHz	-	3	-	Ω
Maximum Body-Diode Continuous Current	I_S		-	-	40	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=15V, V_{GS}=0V, f=1MHz	-	1320	-	pF
Output Capacitance	C_{oss}		-	185	-	
Reverse Transfer Capacitance	C_{rss}		-	170	-	
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V, V_{DS}=15V, I_D=15A	-	27	-	nC
Gate-Source Charge	Q_{gs}		-	5	-	
Gate-Drain Charge	Q_{gd}		-	7	-	
Reverse Recovery Charge	Q_{rr}	I_F=15A, di/dt=100A/us	-	157	-	nC
Reverse Recovery Time	t_{rr}		-	130	-	ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V, V_{DD}=15V, ID=15A R_{GEN}=2.2Ω	-	10.8	-	ns
Turn-on Rise Time	t_r		-	64.8	-	
Turn-off Delay Time	$t_{D(off)}$		-	22.5	-	
Turn-off fall Time	t_f		-	3.7	-	

A. Repetitive rating; pulse width limited by max. junction temperature.
B. NMOS(Die1): T_J=25℃, V_G=10V, R_G=25Ω, L=0.5mH, IAS=13A.
NMOS(Die2): T_J=25℃, V_G=10V, R_G=25Ω, L=0.5mH, IAS=15.5A.
C. P_d is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.
D. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in the still air environment with T_A =25℃. The maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design.

■ NMOS(Die1) Typical Electrical and Thermal Characteristics Diagrams

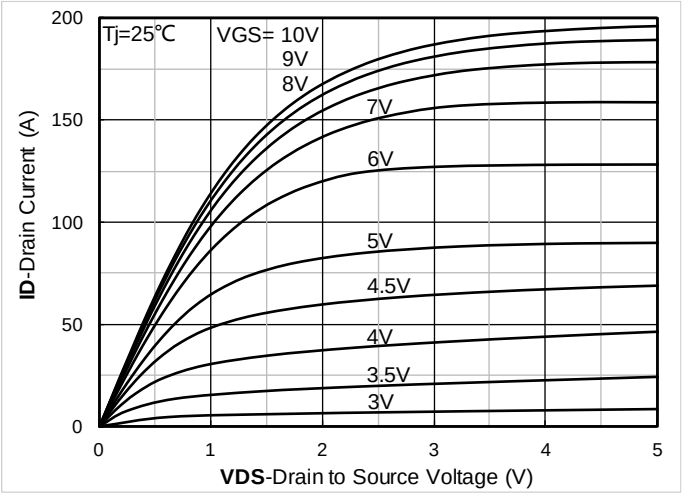


Figure 1. Output Characteristics

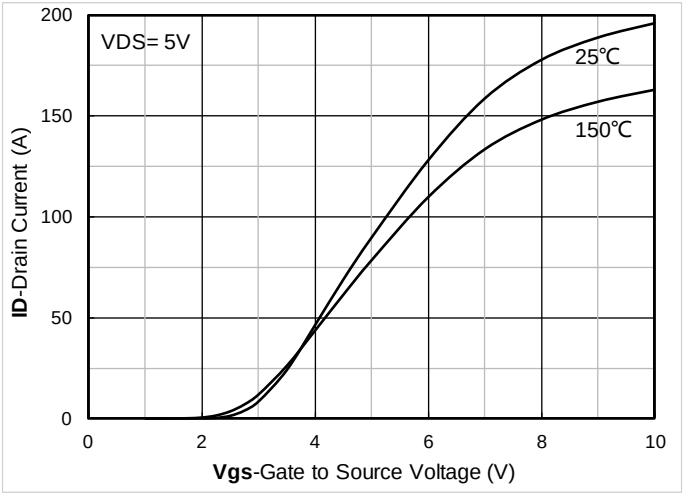


Figure 2. Transfer Characteristics

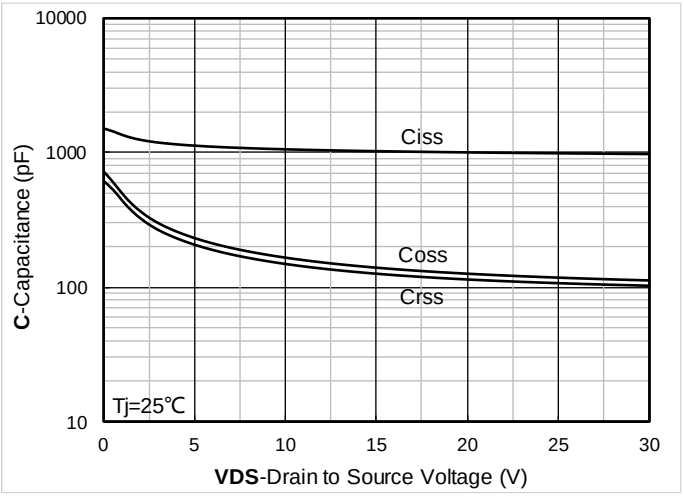


Figure 3. Capacitance Characteristics

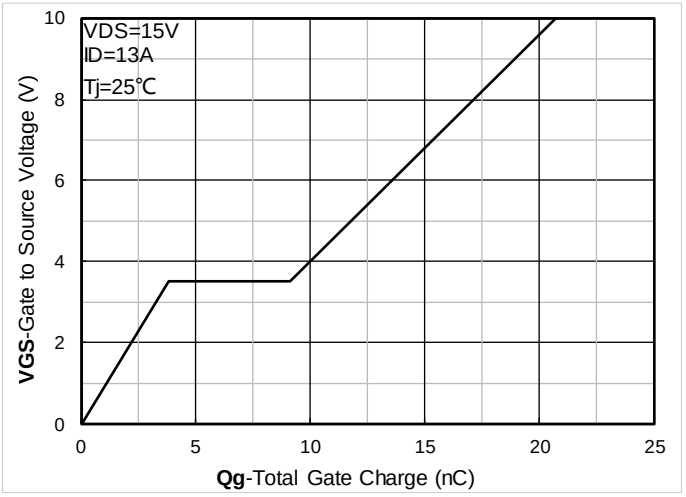


Figure 4. Gate Charge

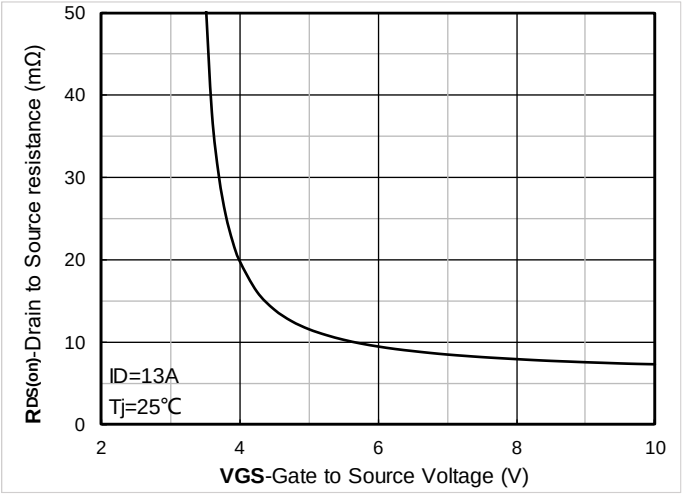


Figure 5. On-Resistance vs Gate to Source Voltage

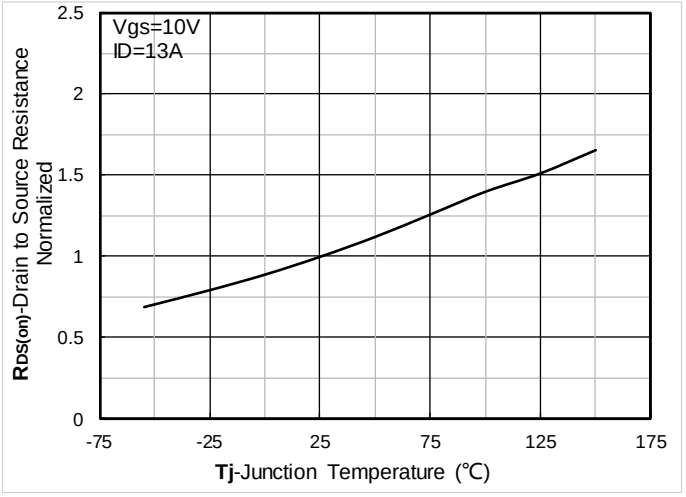


Figure 6. Normalized On-Resistan

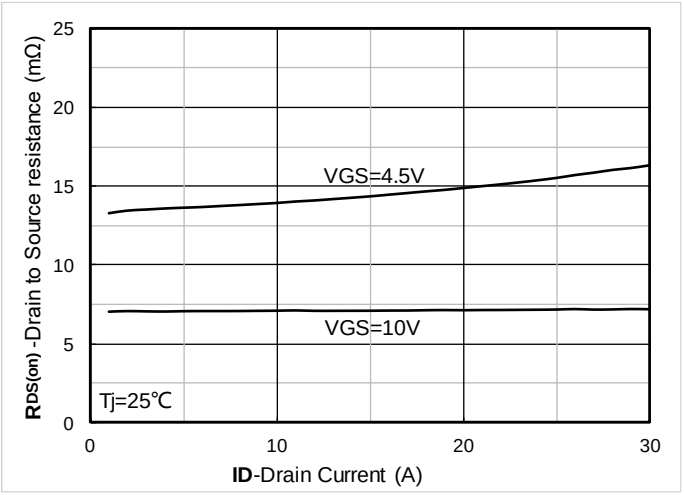


Figure 7. $R_{DS(on)}$ VS Drain Current

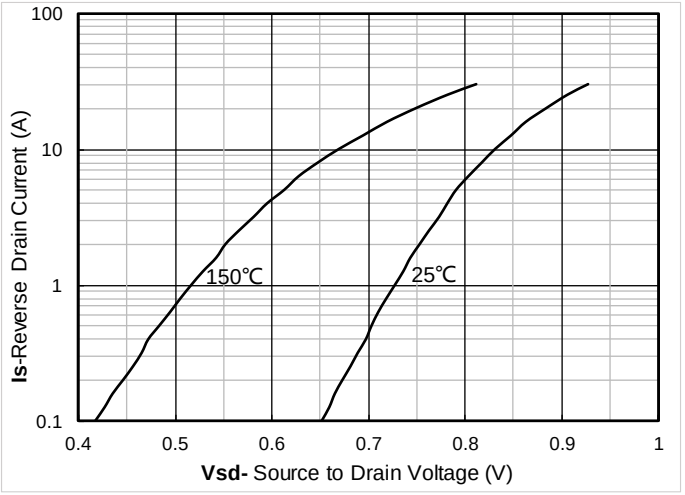


Figure 8. Forward characteristics of reverse diode

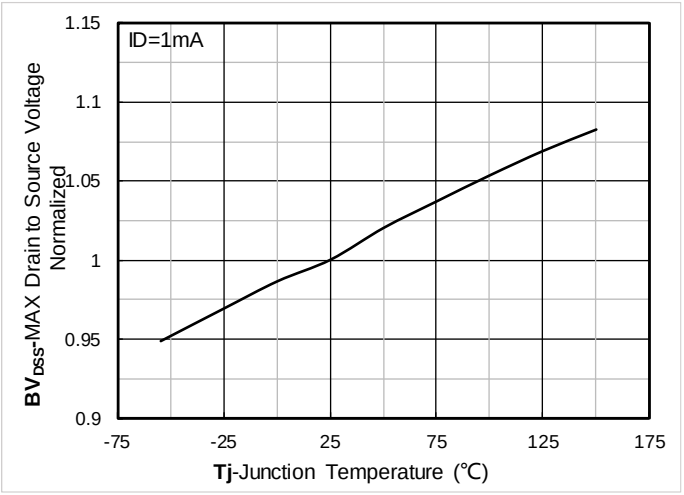


Figure 9. Normalized breakdown voltage

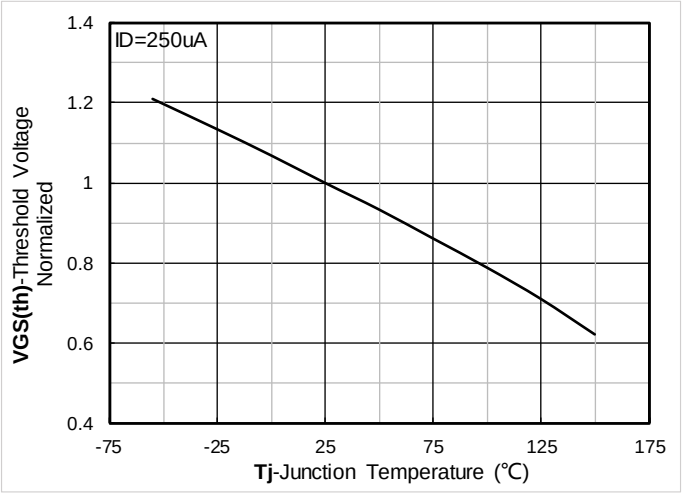


Figure 10. Normalized Threshold voltage

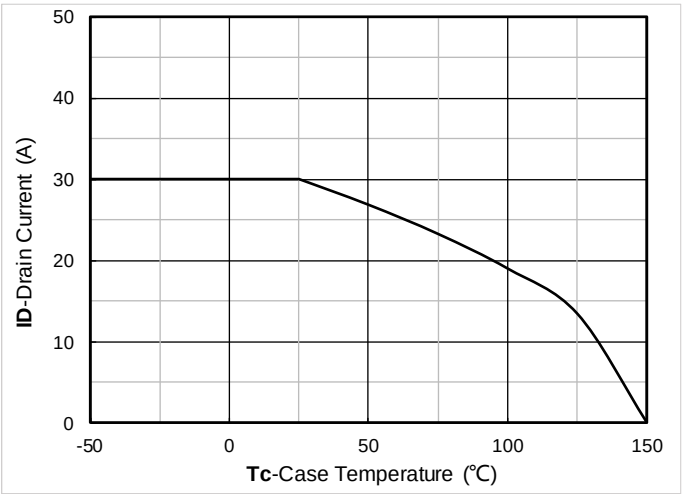


Figure 11. Current dissipation

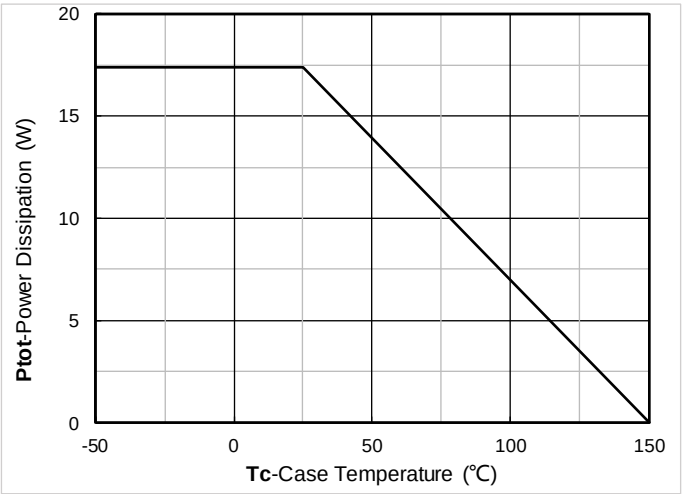


Figure 12. Power dissipation

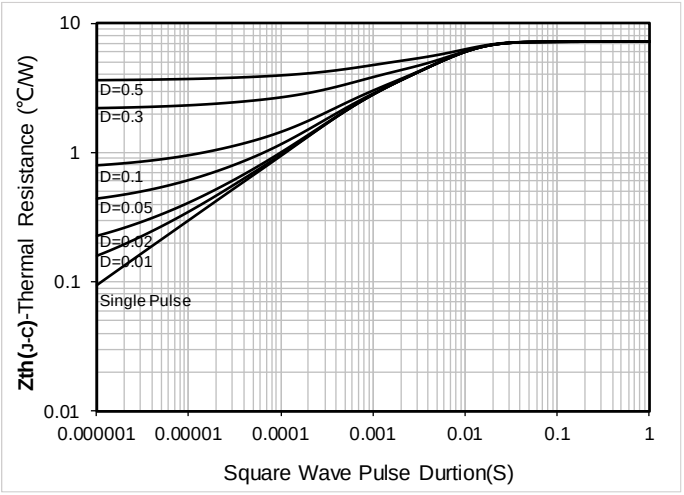


Figure 13. Maximum Transient Thermal Impedance

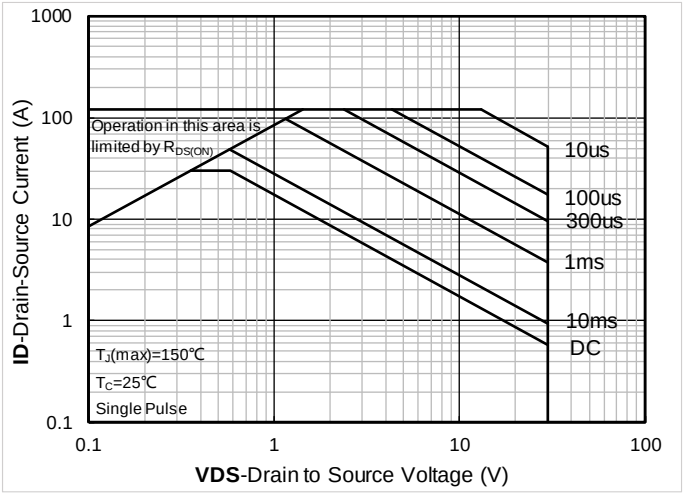


Figure 14. Safe Operation Area

■ NMOS(Die2) Typical Electrical and Thermal Characteristics Diagrams

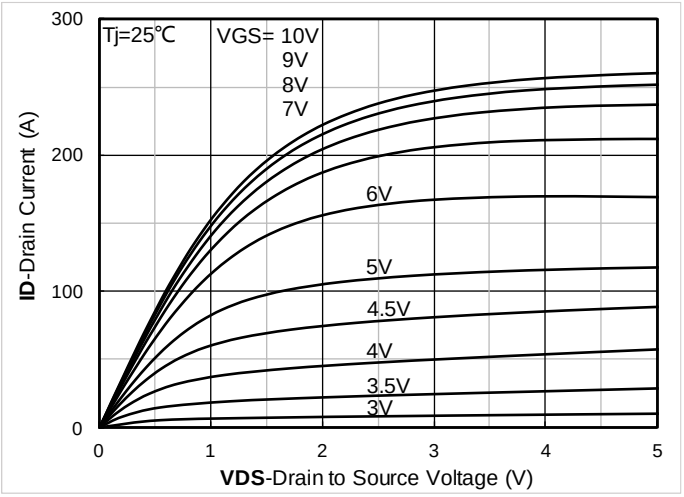


Figure 1. Output Characteristics

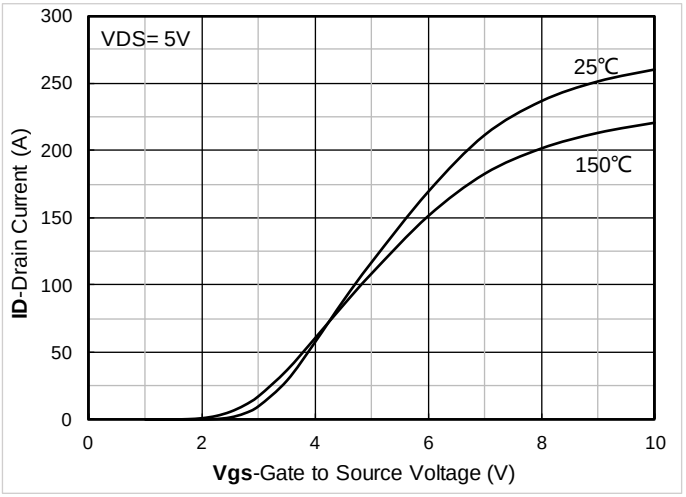


Figure 2. Transfer Characteristics

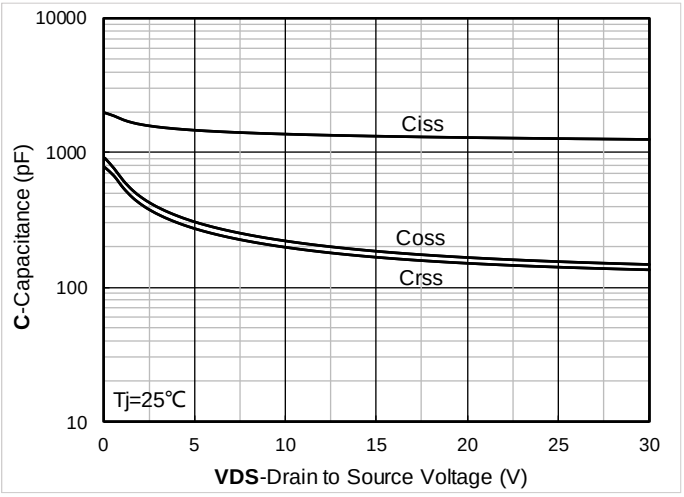


Figure 3. Capacitance Characteristics

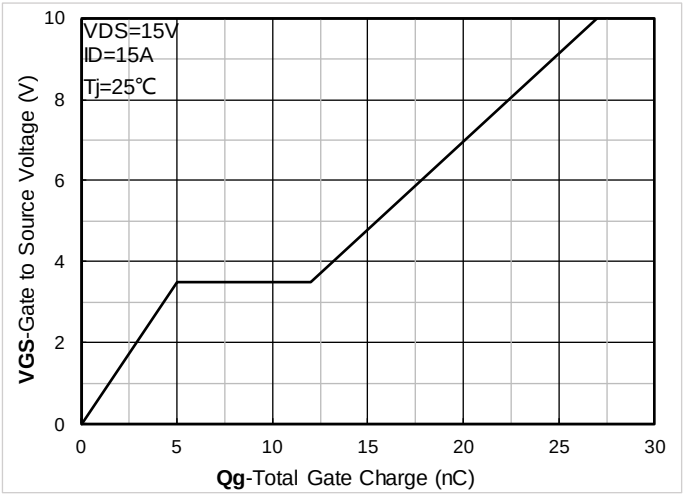


Figure 4. Gate Charge

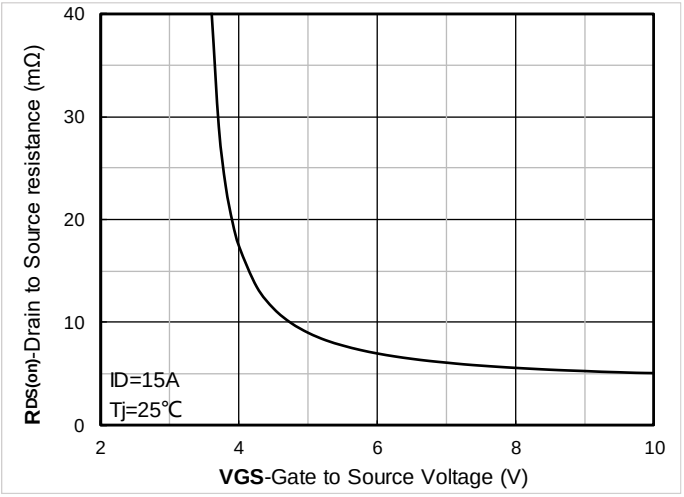


Figure 5. On-Resistance vs Gate to Source Voltage

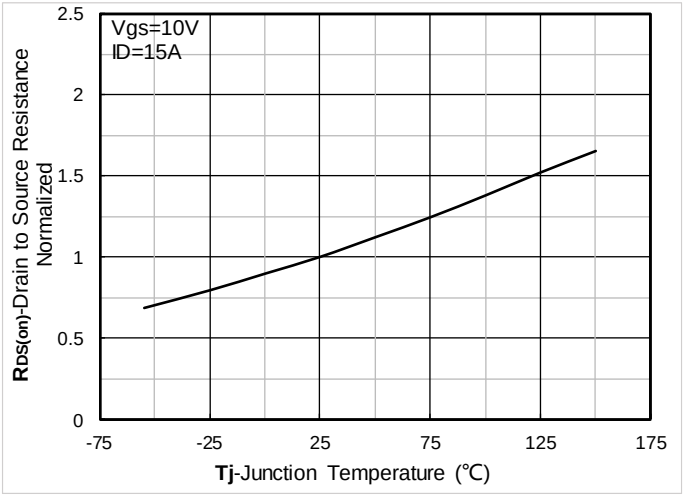


Figure 6. Normalized On-Resistance

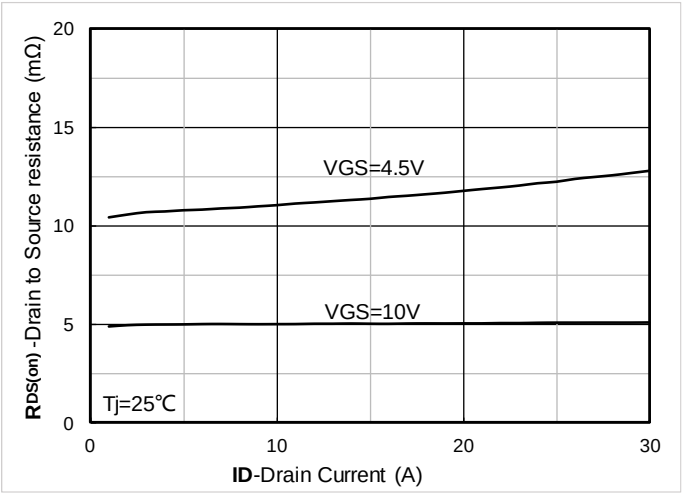


Figure 7. $R_{DS(on)}$ VS Drain Current

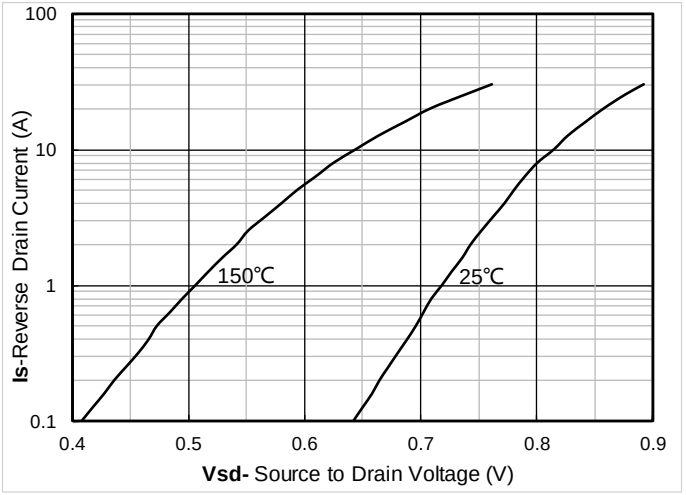


Figure 8. Forward characteristics of reverse diode

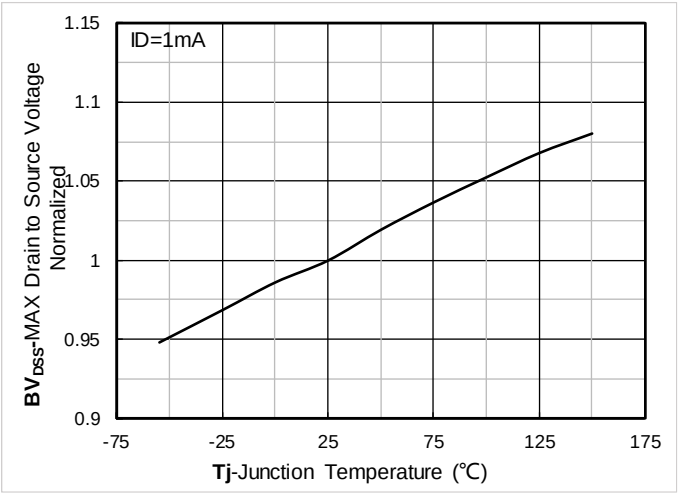


Figure 9. Normalized breakdown voltage

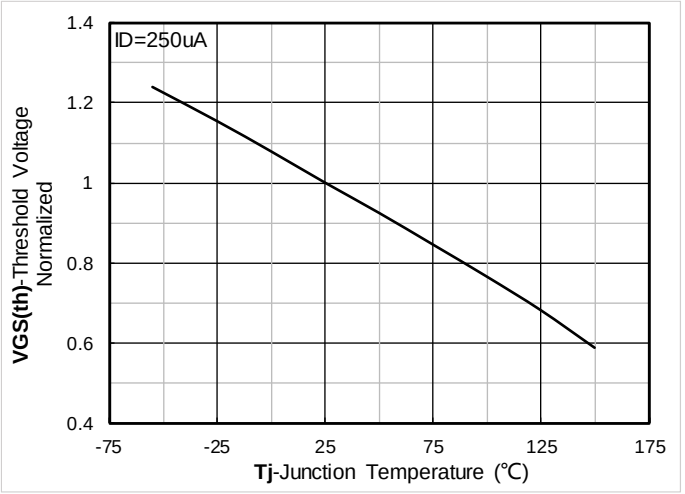


Figure 10. Normalized Threshold voltage

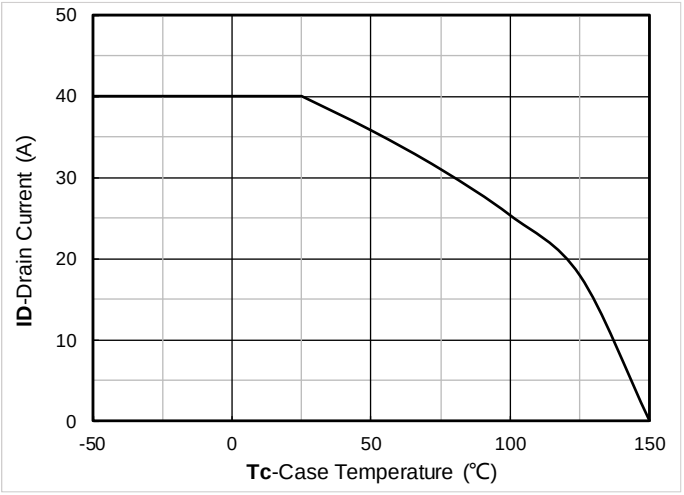


Figure 11. Current dissipation

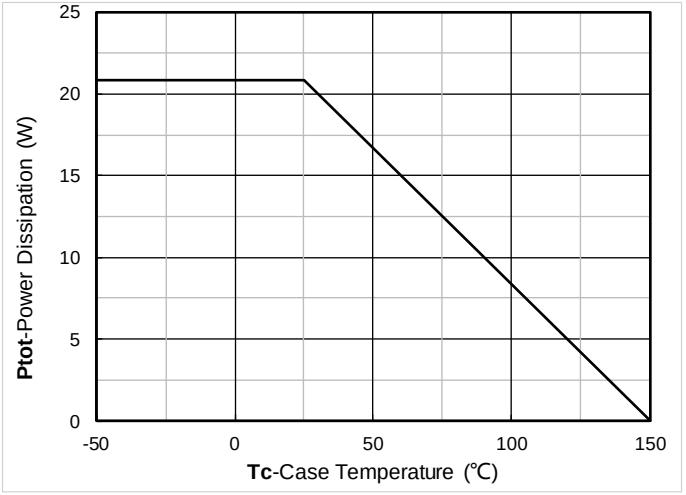


Figure 12. Power dissipation

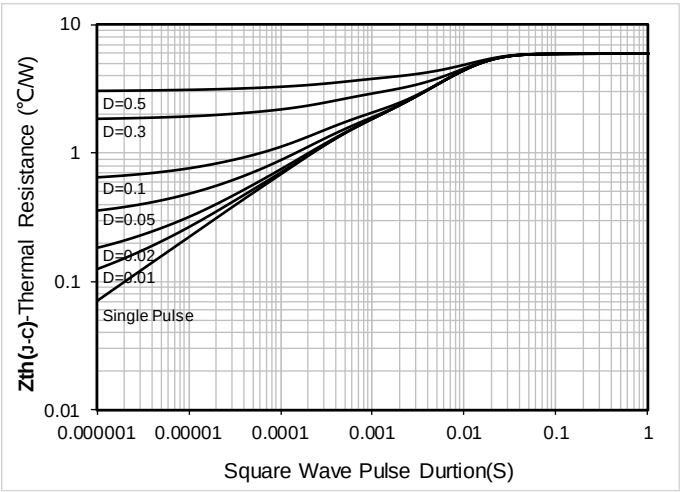


Figure 13. Maximum Transient Thermal Impedance

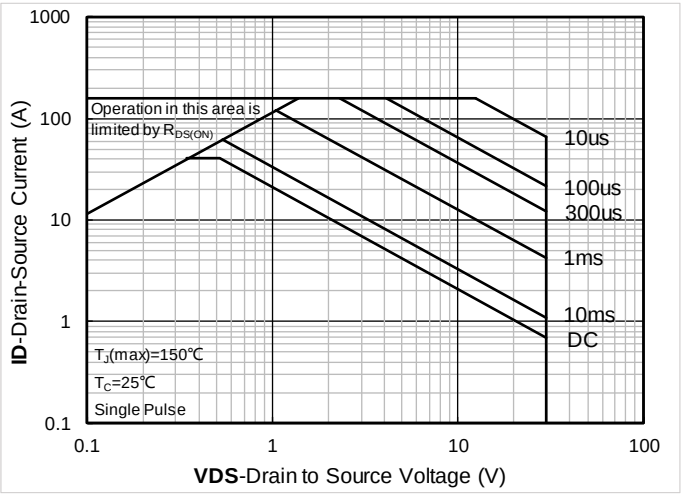
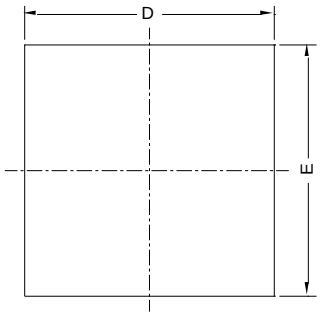
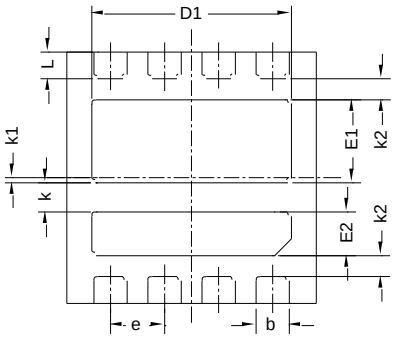


Figure 14. Safe Operation Area

■ DFN3030-8L Package information

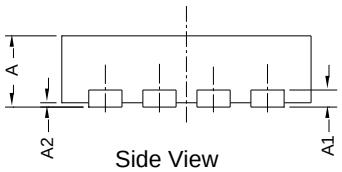


Top View
正面视图

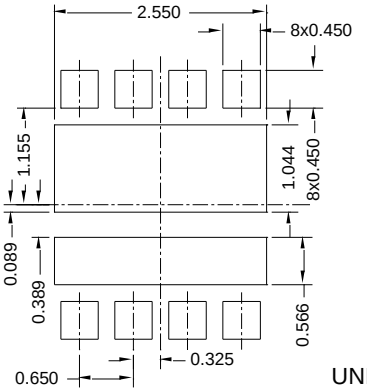


Bottom View
背面视图

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	2.90	3.00	3.10
E	2.90	3.00	3.10
A	0.70	0.80	0.90
A1		0.20 BSC	
A2			0.10
D1	2.30	2.40	2.50
E1	0.89	0.99	1.09
E2	0.42	0.52	0.62
L	0.22	0.32	0.42
k		0.35 BSC	
k1		0.06 BSC	
k2		0.25 BSC	
b	0.30	0.40	0.50
e		0.65 BSC	



Side View
侧面视图



UNIT:mm

Suggested Solder Pad Layout
Top View

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

Notice

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